

Lecture 9: Combinational Circuit Design

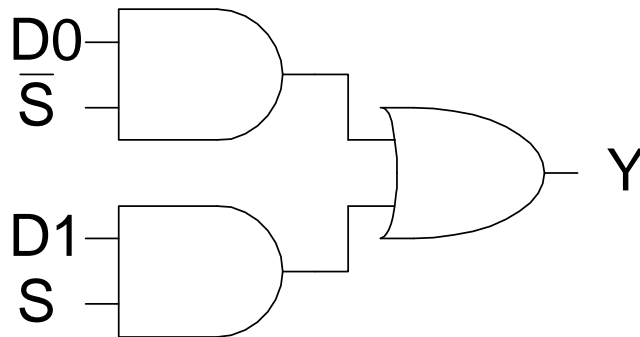
Outline

- Bubble Pushing
- Compound Gates
- Logical Effort Example
- Input Ordering
- Asymmetric Gates
- Skewed Gates
- Best P/N ratio

Example 1

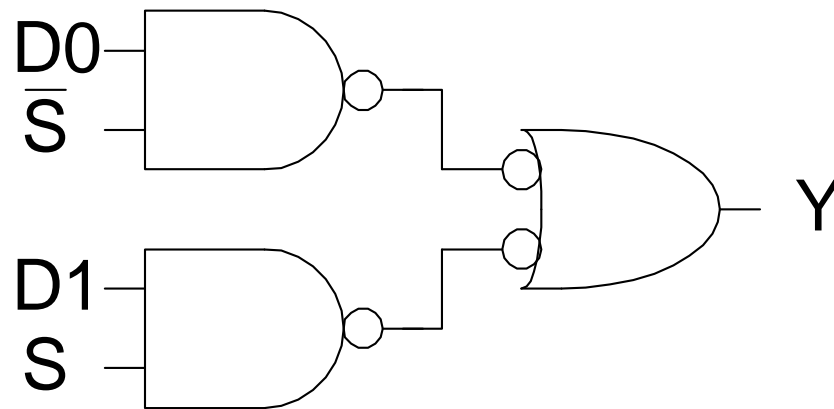
```
module mux(input s, d0, d1,  
           output y);  
  
    assign y = s ? d1 : d0;  
endmodule
```

1) Sketch a design using AND, OR, and NOT gates.



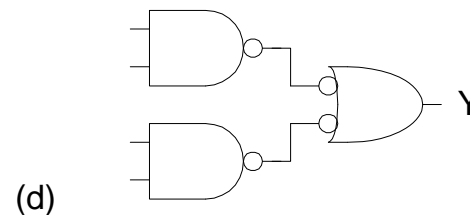
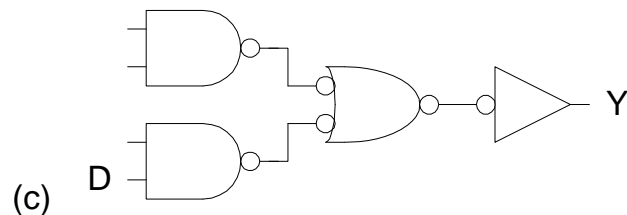
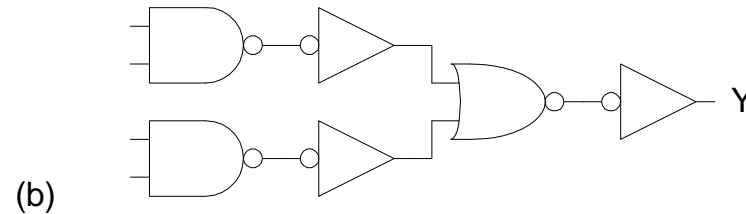
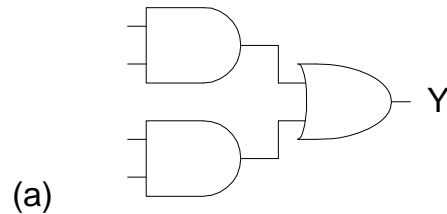
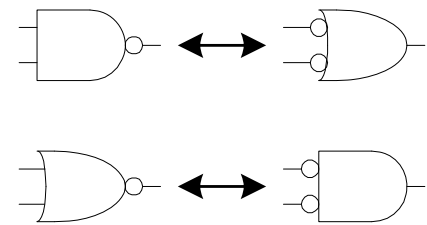
Example 2

2) Sketch a design using NAND, NOR, and NOT gates.
Assume $\sim S$ is available.



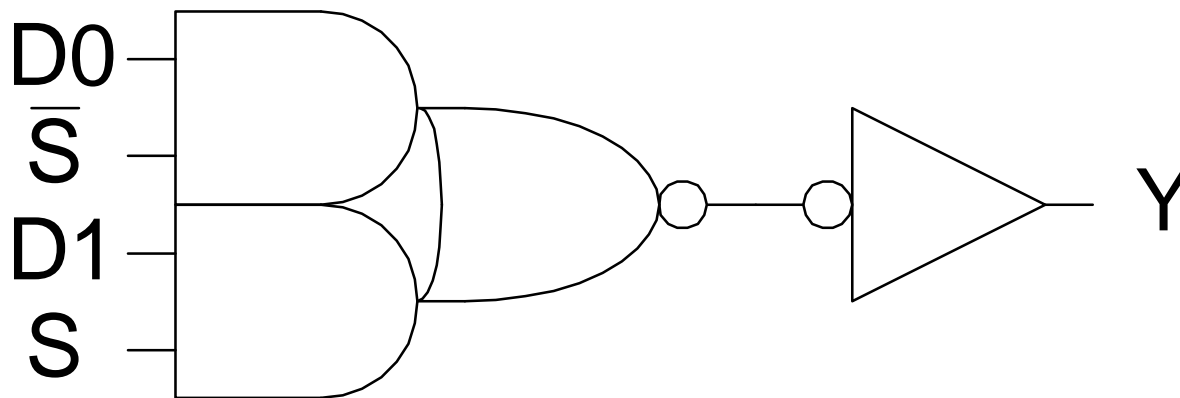
Bubble Pushing

- ❑ Start with network of AND / OR gates
- ❑ Convert to NAND / NOR + inverters
- ❑ Push bubbles around to simplify logic
 - Remember DeMorgan's Law



Example 3

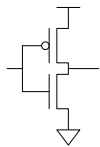
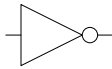
3) Sketch a design using one compound gate and one NOT gate. Assume $\sim S$ is available.



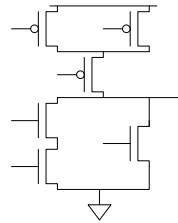
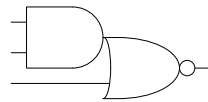
Compound Gates

Logical Effort of compound gates

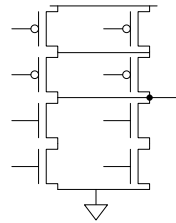
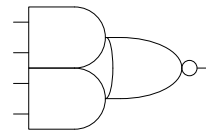
$$Y = \bar{A}$$



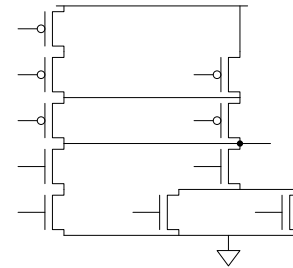
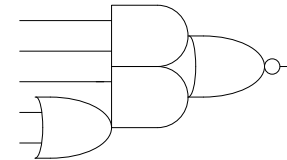
$$Y = \overline{A \cdot B + C}$$



$$Y = \overline{A \cdot B + C \cdot D}$$



$$Y = \overline{A \cdot (B + C) + D \cdot E}$$



unit inverter

AO

A

Y

A
B
C

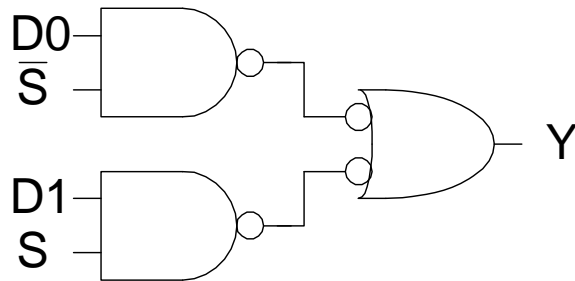
Y

A
B
C
D

Example 4

- The multiplexer has a maximum input capacitance of 16 units on each input. It must drive a load of 160 units. Estimate the delay of the two designs.

H =



$P =$

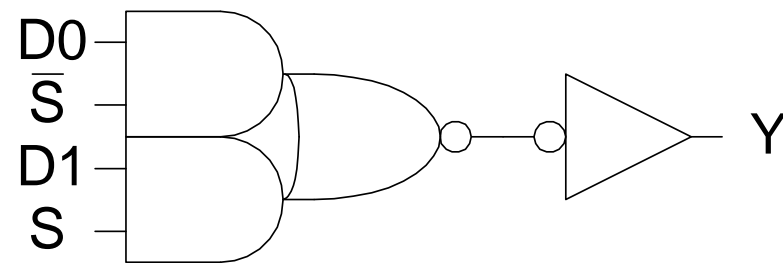
$G =$

$F =$

$\hat{f} =$

$D =$

B = N =



$P =$

$G =$

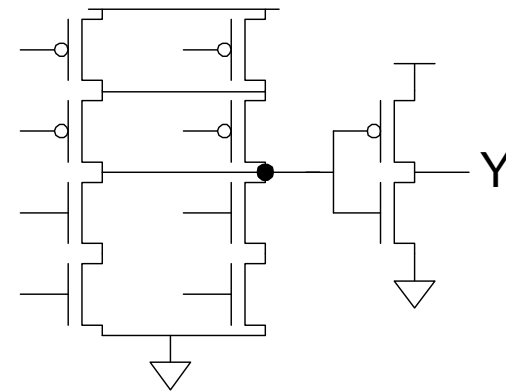
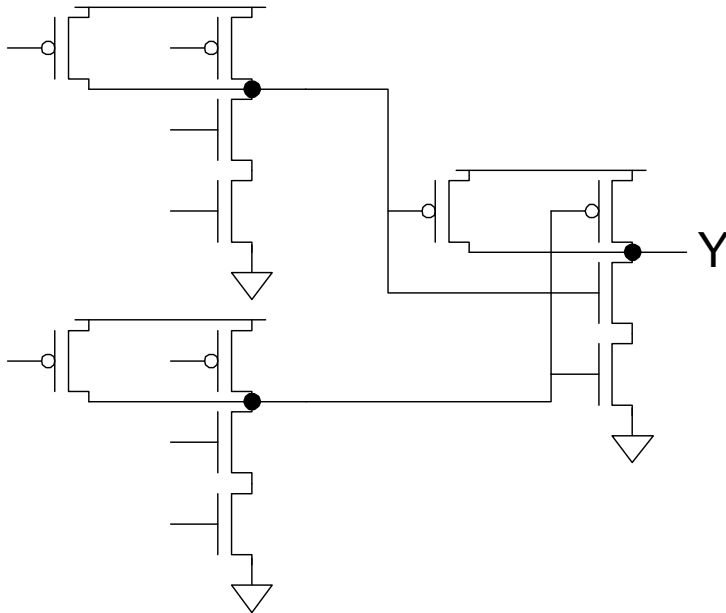
$F =$

$\hat{f} =$

$D =$

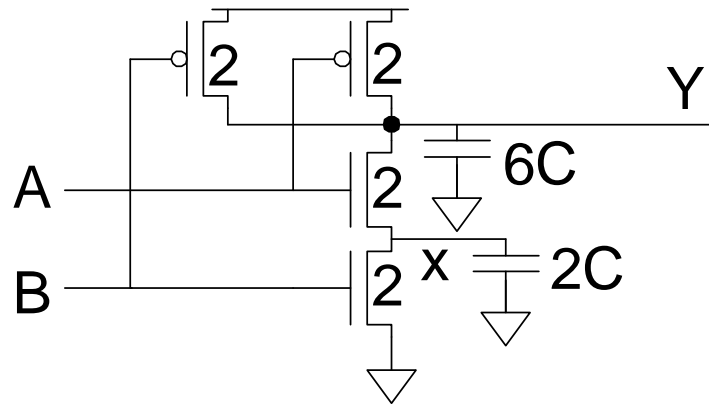
Example 5

- Annotate your designs with transistor sizes that achieve this delay.



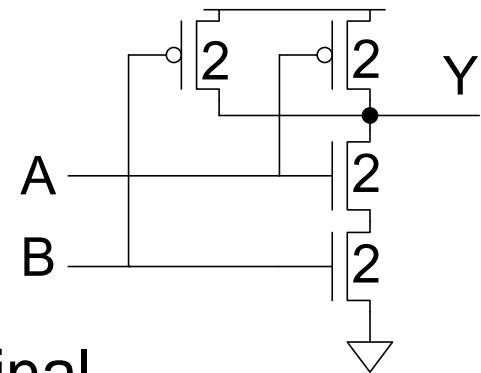
Input Order

- ❑ Our parasitic delay model was too simple
 - Calculate parasitic delay for Y falling
 - If A arrives latest?
 - If B arrives latest?



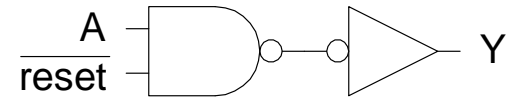
Inner & Outer Inputs

- ❑ *Inner* input is closest to output (A)
- ❑ *Outer* input is closest to rail (B)
- ❑ If input arrival time is known
 - Connect latest input to inner terminal

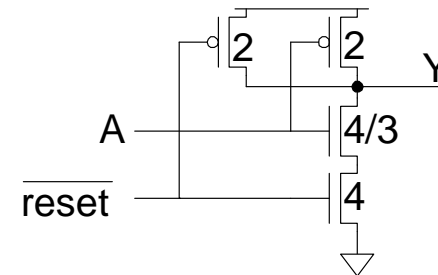


Asymmetric Gates

- ❑ Asymmetric gates favor one input over another
- ❑ Ex: suppose input A of a NAND gate is most critical
 - Use smaller transistor on A (less capacitance)
 - Boost size of noncritical input
 - So total resistance is same

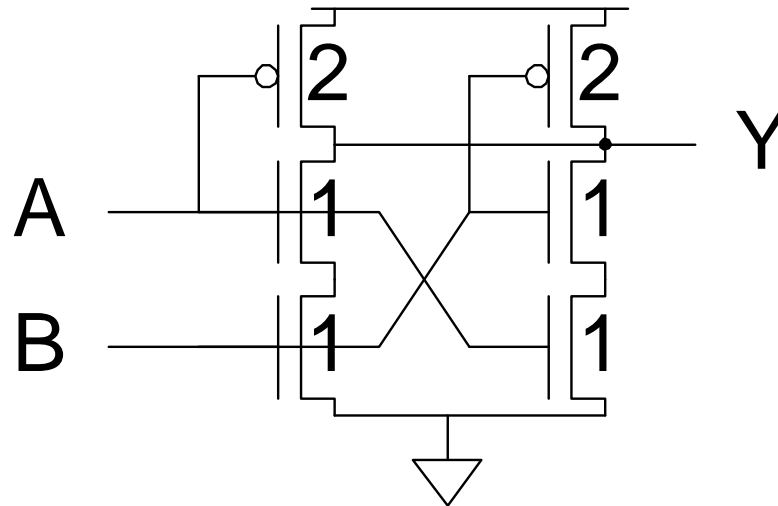


- ❑ $g_A =$
- ❑ $g_B =$
- ❑ $g_{\text{total}} = g_A + g_B =$
- ❑ Asymmetric gate approaches $g = 1$ on critical input
- ❑ But total logical effort goes up



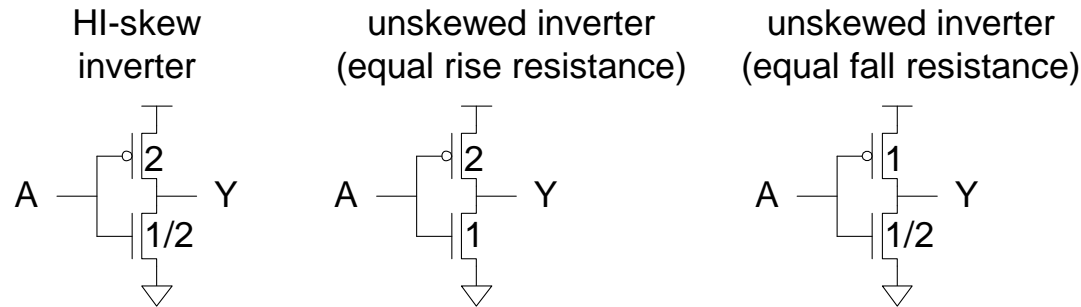
Symmetric Gates

- Inputs can be made perfectly symmetric



Skewed Gates

- ❑ Skewed gates favor one edge over another
- ❑ Ex: suppose rising output of inverter is most critical
 - Downsize noncritical nMOS transistor



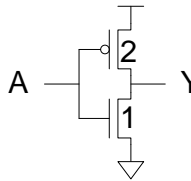
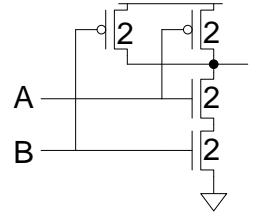
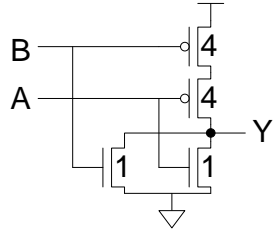
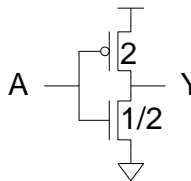
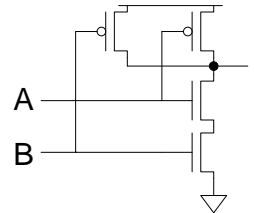
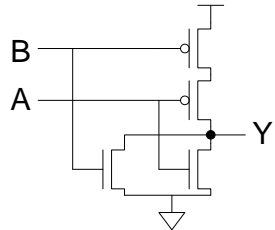
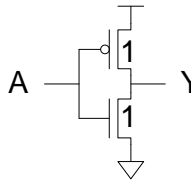
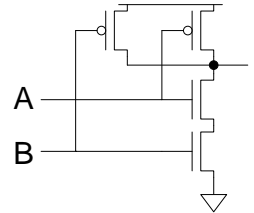
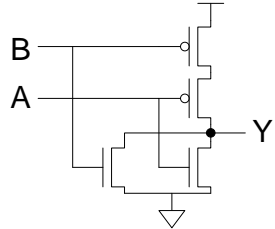
- ❑ Calculate logical effort by comparing to unskewed inverter with same effective resistance on that edge.
 - $g_u =$
 - $g_d =$

HI- and LO-Skew

- ❑ Def: Logical effort of a skewed gate for a particular transition is the ratio of the input capacitance of that gate to the input capacitance of an unskewed inverter delivering the same output current for the same transition.

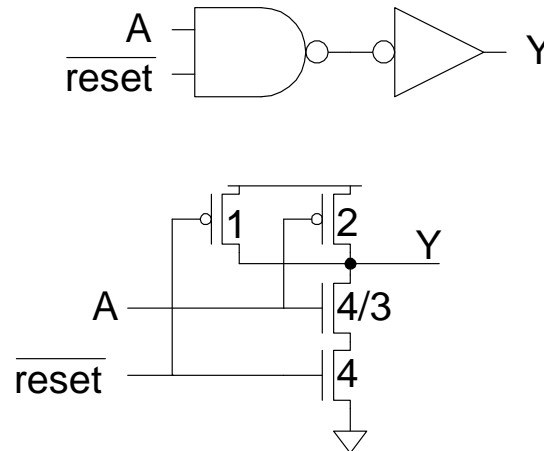
- ❑ Skewed gates reduce size of noncritical transistors
 - HI-skew gates favor rising output (small nMOS)
 - LO-skew gates favor falling output (small pMOS)
- ❑ Logical effort is smaller for favored direction
- ❑ But larger for the other direction

Catalog of Skewed Gates

	Inverter	NAND2	NOR2
unskewed	 $g_u = 1$ $g_d = 1$ $g_{avg} = 1$	 $g_u = 4/3$ $g_d = 4/3$ $g_{avg} = 4/3$	 $g_u = 5/3$ $g_d = 5/3$ $g_{avg} = 5/3$
HI-skew	 $g_u = 5/6$ $g_d = 5/3$ $g_{avg} = 5/4$	 $g_u =$ $g_d =$ $g_{avg} =$	 $g_u =$ $g_d =$ $g_{avg} =$
LO-skew	 $g_u = 4/3$ $g_d = 2/3$ $g_{avg} = 1$	 $g_u =$ $g_d =$ $g_{avg} =$	 $g_u =$ $g_d =$ $g_{avg} =$

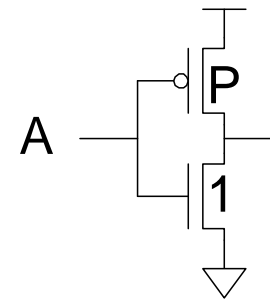
Asymmetric Skew

- ❑ Combine asymmetric and skewed gates
 - Downsize noncritical transistor on unimportant input
 - Reduces parasitic delay for critical input



Best P/N Ratio

- ❑ We have selected P/N ratio for unit rise and fall resistance ($\mu = 2-3$ for an inverter).
- ❑ Alternative: choose ratio for least average delay
- ❑ Ex: inverter
 - Delay driving identical inverter
 - $t_{pdf} =$
 - $t_{pdr} =$
 - $t_{pd} =$
 - $dt_{pd} / dP =$
 - Least delay for $P =$

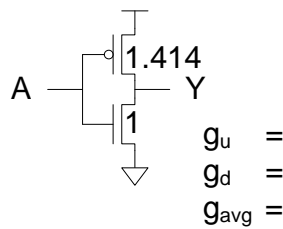


P/N Ratios

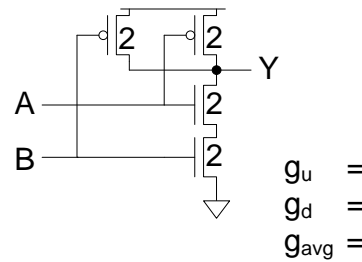
- In general, best P/N ratio is sqrt of equal delay ratio.
 - Only improves average delay slightly for inverters
 - But significantly decreases area and power

fastest
P/N ratio

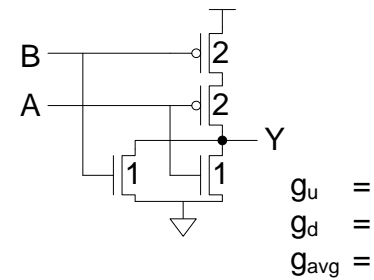
Inverter



NAND2



NOR2



Observations

- ❑ For speed:
 - NAND vs. NOR
 - Many simple stages vs. fewer high fan-in stages
 - Latest-arriving input
- ❑ For area and power:
 - Many simple stages vs. fewer high fan-in stages